



PATENT APPLICATION
Docket No. 9898-321
Client No. SS-18146-US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Ki-Yeon Park, et al. Conf. No. 8248
Serial No. 10/713,577 Examiner: Not yet assigned
Filed: November 12, 2003 Art Unit: 2818
For: CAPACITOR OF SEMICONDUCTOR MEMORY DEVICE THAT HAS
COMPOSITE $\text{Al}_2\text{O}_3/\text{HfO}_2$ DIELECTRIC LAYER AND METHOD OF
MANUFACTURING THE SAME

INFORMATION DISCLOSURE CITATION
FORM PTO-1449 (Modified)

U.S. PATENT DOCUMENTS

Exam Init	Ref	Document Number	Issue Date	Name	Class	Sub Class
<u>PR</u>		2002/0115252	Aug. 22, 02	Haukka et al.		

INFORMATION DISCLOSURE CITATION
FORM PTO-1449 (Modified)

FOREIGN PATENT DOCUMENTS

Exam Init	Ref	Publication Number	Publication Date	Country	Name
<u>PR</u>		P2001-0082118	Aug. 29, 01	Korea	

OTHER DOCUMENTS

Exam Init	Ref	Author, Title, Date, Pertinent Pages, Etc.)
<u>PR</u>		English Language Abstract of Korean Publication No: P2001-0082118

Examiner: *[Signature]*

Date Considered: 12/1/04



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<u>PA</u>	—	P2002-0002596	Jan. 10, 2002	Korea	
<u>PA</u>	—	P2002-0034520	May 9, 2002	Korea	

OTHER DOCUMENTS

<u>Exam Init</u>	<u>Ref</u>	<u>Author, Title, Date, Pertinent Pages, Etc.)</u>
<u>PA</u>	—	English Language Abstract of Korean Publication No: P2002-0002596
<u>PA</u>	—	English Language Abstract of Korean Publication No: P2002-0034520

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